

2013年度発表

主発表者	所属	発表先	タイトル	課題番号
T.Yamashita	R&D Partnership for Future Power Electronics Technology (FUPET) [SHOWA DENKO K.K.]	Materials Science Forum, 778-780 (2014), 374-377	Origin Analyses of Trapezoid-Shape Defects in 4-deg.-off 4H-SiC Epitaxial Wafers by Synchrotron X-ray Topography	1105051AS 1204021A 1303011S 1303017A
Hideki Sako	R&D Partnership for Future Power Electronics Technology (FUPET)	Materials Science Forum, 778-780 (2014), 370-373	Microstructural analysis of damaged layer introduced during chemo-mechanical polishing	1204021A 1303011S 1303017A
Keiko Masumoto	R & D Partnership for Future Power Electronics Technology [Advanced Power Electronics Research Center, National Institute of Advanced Industrial Science and Technology]	Materials Science Forum, 778-780 (2014), 99-102	Conversion of basal plane dislocations to threading edge dislocations in growth of epitaxial layers on 4H-SiC substrates with vicinal off-angle	1204021A 1303017A
Shiyang Ji	Advanced Power Electronics Research Center (ADPERC), National Institute of Advanced Industrial Science and Technology	Materials Science Forum, 778-780 (2014), 151-154	Characterization of the defect evolution in thick heavily Al-doped 4H-SiC epilayers	1204021A 1303017A
Masayuki Sasaki	R&D Partnership for Future Power Electronics Technology (FUPET) [Advanced Power Electronics Research Center, National Institute of Advanced Industrial Science and Technology]	Materials Science Forum, 778-780 (2014), 398-401	Analysis on generation of localized step bunching on 4H-SiC(0001)Si-face by synchrotron X-ray topography	1204021A 1303017A
Junji Matsunaga	Nippon Nuclear Fuel Development Co. Ltd.	Journal of Nuclear Science and Technology, 51 (2014), 1231-1240	Dependence of vacancy concentration on morphology of helium bubbles in oxide ceramics	1205039S 1208081R 1211127R
Mikihiko Nishitani	Panasonic Device Science Research Alliance Laboratory Osaka University	Material Research Society Symp. Proc. , 1538 (2013), 399-404	The Wide band p- type material formed by the thin film with ZnO - NiO mixed crystal system	1301156R
Rui Wena	Byon Initiative Research Unit (IRU), RIKEN	Chemical Communications, 50 (2014), 2628-2631	In situ Monitoring of Li-O ₂ Electrochemical Reaction on Nanoporous Gold using Electrochemical AFM	1310118PT 1310119R

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Fengxia Geng	International Center for Materials Nanoarchitectonics, National Institute for Materials Science	Journal of the American Chemical Society, 136(14) (2014), 5491–5500	Gigantic Swelling of Inorganic Layered Materials: A Bridge to Molecularly Thin Two-Dimensional Nanosheets	1101137N 1311158F 1405034S 1408094S
Kazuya Idemitsu	Kyushu University	Advances in Materials Science for Environmental and Energy Technologies II, Vol. 241 (2013), 23–34	Migration of Iodine Solidified in Ettringite into Compacted Bentonite	1012002AS
Ayuko Kitajou	Research and Education Center of Carbon Resources, Kyushu University	Journal of Power Sources, 243 (2013), 494–498	Synthesis of FeOF using roll-quenching method and the cathode properties for lithium-ion battery	1109087N
Ayuko Kitajou	Research and Education Center of Carbon Resources, Kyushu University	Journal of Power Sources, 247 (2014), 391–395	Discharge/charge reaction mechanism of a pyrite-type FeS ₂ cathode for sodium secondary batteries	1011112N 1110096N
Yusuke Iguchi	Kumamoto University Innovative Collaboration Organization, Kumamoto University	Philosophical Magazine Letters, Volume 93 (2013),	Tailoring of interfaces in amorphous silicon-germanium multilayers on the atomic scale by ultra-high gravity	100884N 100411N
Sausan Al-Riyami	Department of Applied Science for Electronics and Materials, Kyushu University	ECS Journal of Solid State Science and Technology, 2 (2013), M33–38	Chemical Bonding of Nitrogenated Ultrananocrystalline Diamond Films Deposited on Titanium Substrates by Pulsed Laser Deposition	–
Sausan Al-Riyami	Department of Applied Science for Electronics and Materials, Kyushu University	Japanese Journal of Applied Physics, 52 (2013), 06GG06	Effects of Hydrogen and Nitrogen Atmospheres on Growth of Ultrananocrystalline Diamond/Amorphous Carbon Composite Films by Reactive Pulsed Laser Deposition	–
Yūki Katamune	Department of Applied Science for Electronics and Materials, Kyushu University	Japanese Journal of Applied Physics, 52 (2013), 065801	Heterojunction Diodes Comprising p-Type Ultrananocrystalline Diamond Films Prepared by Coaxial Arc Plasma Deposition and n-Type Silicon Substrates	–
Sausan Al-Riyami	Department of Applied Science for Electronics and Materials, Kyushu University	ECS Journal of Solid State Science and Technology, 50 (2013), 41–47	Nitrogenation Effects on n-Type Electrical Conductivity of Ultrananocrystalline Diamond/Hydrogenated Amorphous Carbon Composite Films Prepared by Pulsed Laser Deposition	–

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Yuki Katamune	Department of Applied Science for Electronics and Materials, Kyushu University	ECS Journal of Solid State Science and Technology, 50 (2013), 23-28	Formation of p-Type Ultrananocrystalline Diamond/Nonhydrogenated Amorphous Carbon Composite Films Prepared by Coaxial Arc Plasma Deposition with Boron-Incorporated Graphite Targets	-
Nathaporn Promros	Department of Physics, Faculty of Science, King Mongkut's Institute of Technology Ladkrabang	Advanced Materials Research, 858 (2013), 171-176	Temperature Dependent Current-Voltage Characteristics of n-Type Nanocrystalline-FeSi ₂ /p-Type Si Heterojunctions Fabricated by Pulsed Laser Deposition	-
Nathaporn Promros	Department of Physics, Faculty of Science, King Mongkut's Institute of Technology Ladkrabang	Applied Mechanics and Materials, 446-447 (2014), 88-92	Electrical Characteristics of n-Type Nanocrystalline FeSi ₂ /Intrinsic Si/p-Type Si Heterojunctions Prepared by Facing-Targets Direct-Current Sputtering	-
Nathaporn Promros	Department of Physics, Faculty of Science, King Mongkut's Institute of Technology Ladkrabang	Advanced Materials Research, 802 (2013), 199-203	Current Transport Mechanism of n-Type Nanocrystalline FeSi ₂ /Intrinsic Si/p-Type Si Heterojunctions Fabricated by Facing-Targets Direct-Current Sputtering	-
Nathaporn Promros	Department of Physics, Faculty of Science, King Mongkut's Institute of Technology Ladkrabang	Advanced Materials Research, 747 (2013), 217-220	Characterizations of Mesa Structural Near-Infrared n-Type Nanocrystalline-FeSi ₂ /p-Type Si Heterojunction Photodiodes at Low Temperatures	-
Nathaporn Promros	Department of Physics, Faculty of Science, King Mongkut's Institute of Technology Ladkrabang	Applied Mechanics and Materials, 446-447 (2014), 88-92	Electrical Characteristics of n-Type Nanocrystalline FeSi ₂ /Intrinsic Si/p-Type Si Heterojunctions Prepared by Facing-Targets Direct-Current Sputtering	-
Yusril Yusuf	Physics Department, Faculty of Mathematics and Natural Sciences, Gadjah Mada University	Advances in Condensed Matter Physic, 2013 (2013), 752060, 11page	Polar Liquid Crystal Elastomers Cross Linked Far from Thermodynamic Phase Transitions: Dislocation Loops in Smectic Clusters	100772AS
Kazutoshi Takahashi	Department of Electrical & Electronic Engineering, Saga University	Applied Physics Letters, 104 (2014), 072101	Electronic states of NO ₂ -exposed H-terminated diamond/Al ₂ O ₃ heterointerface studied by synchrotron radiation photoemission and X-ray absorption spectroscopy	-